

## L735-06-55 Infrared LED Lamp for High Current Drive

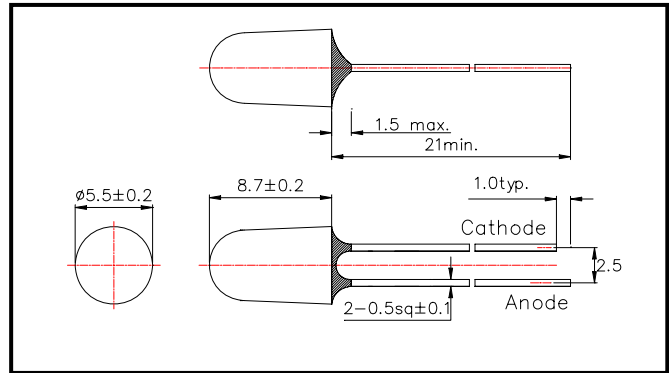
L735-06-55 is an AlGaAs LED mounted on a lead frame with a clear epoxy lens.

On forward bias, it emits a spectral band of radiation which peaks at 735nm. These devices are intended to be operated at pulsed current of 1A under maximum 4.3V for stable long life.

### ◆ Specifications

- 1) Product Name      Infrared LED Lamp
- 2) Type No.          L735-06-55
- 3) Chip
  - (1) Chip Material      AlGaAs
  - (2) Chip Dimension    550umx550um
  - (3) Peak Wavelength  735nm typ.
- 4) Package
  - (1) Type                Φ5mm clear molding
  - (2) Resin Material    Epoxy Resin
  - (3) Lead Frame        Soldered

### ◆ Outer dimension (Unit: mm)



### ◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	PD	170	mW	Ta=25°C
Forward Current	IF	100	mA	Ta=25°C
Pulse Forward Current	IFP	1000	mA	Ta=25°C
Reverse Voltage	VR	5	V	Ta=25°C
Operating Temperature	TOPR	-30 ~ +85	°C	
Storage Temperature	TSTG	-30 ~ +100	°C	
Soldering Temperature	TSOL	260	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

### ◆ Electro-Optical Characteristics [Ta=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50mA		1.60	1.70	V
	VFP	IF=1000mA		3.5	4.3	
Reverse Current	IR	VR=5V			10	uA
Total Radiated Power	PO	IF=50mA	16.0	20.0		mW
Radiant Intensity	IE	IF=50mA		110		mW/sr
	IEP	IFP=1000mA		2200		
Peak Wavelength	$\lambda_P$	IF=50mA	720	735	750	nm
Half Width	$\Delta\lambda$	IF=50mA		35		nm
Viewing Half Angle	$\theta_{1/2}$	IF=50mA		$\pm 8$		deg.
Rise Time	tr	IF=50mA		80		ns
Fall Time	tf	IF=50mA		80		ns

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.